

N- AND P-Channel Logic Level Enhancement Mode MOSFET

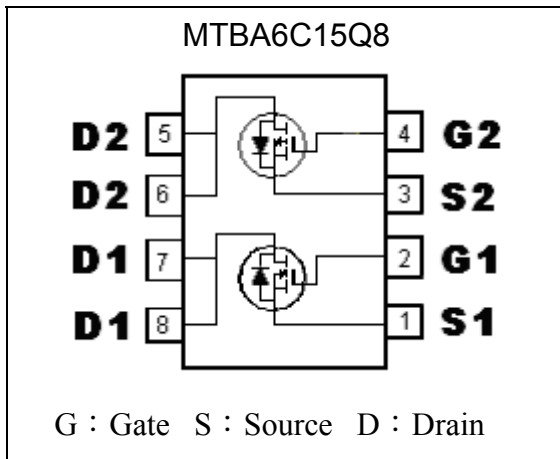
MTBA6C15Q8

	N-CH	P-CH
BV_{DSS}	150V	-150V
$I_D @ T_A=25^{\circ}C, V_{GS}=10V(-10V)$	1.8A	-1.5A
$I_D @ T_A=70^{\circ}C, V_{GS}=10V(-10V)$	1.5A	-1.3A
$I_D @ T_C=25^{\circ}C, V_{GS}=10V(-10V)$	3.2A	-2.6A
$I_D @ T_C=100^{\circ}C, V_{GS}=10V(-10V)$	2.3A	-1.8A
$R_{DSON}(typ.) @ V_{GS}=(-)10V$	169 mΩ	259 mΩ
$R_{DSON}(typ.) @ V_{GS}=(-)4.5V$	176 mΩ	277 mΩ

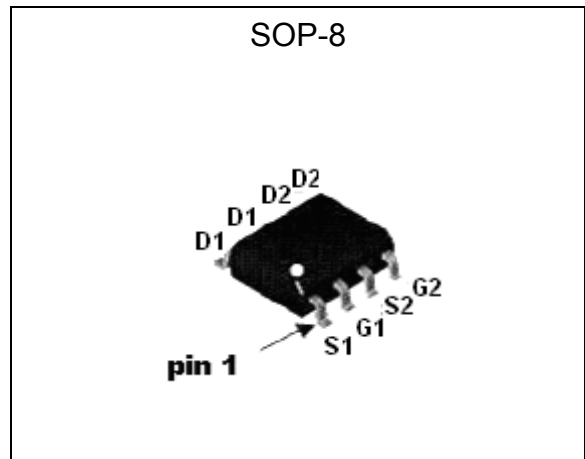
Features

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package

Equivalent Circuit

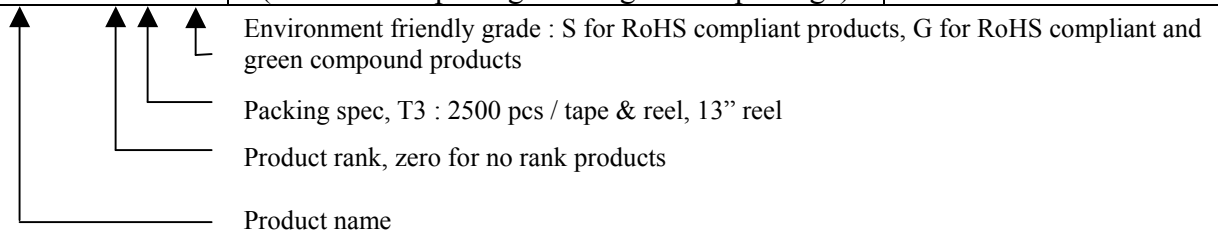


Outline



Ordering Information

Device	Package	Shipping
MTBA6C15Q8-0-T3-G	SOP-8 (Pb-free lead plating & halogen-free package)	2500 pcs / Tape & Reel





Absolute Maximum Ratings ($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Limits		Unit	
		N-channel	P-channel		
Drain-Source Breakdown Voltage	BV_{DSS}	150	-150	V	
Gate-Source Voltage	V_{GS}	± 20	± 20		
Continuous Drain Current	I_D	$T_C=25^{\circ}C, V_{GS}=10V (-10V)$	3.2	-2.6	A
		$T_C=100^{\circ}C, V_{GS}=10V (-10V)$	2.3	-1.8	
Continuous Drain Current (Note 2)	I_{DSM}	$T_A=25^{\circ}C, V_{GS}=10V (-10V)$	1.8	-1.5	
		$T_A=70^{\circ}C, V_{GS}=10V (-10V)$	1.5	-1.3	
Pulsed Drain Current (Note 1)	I_{DM}	10	-8		
Power Dissipation for Dual Operation @ $T_C=25^{\circ}C$	P_D	6		W	
Power Dissipation for Dual Operation @ $T_A=25^{\circ}C$	P_{DSM}	3			
Power Dissipation for Single Operation @ $T_A=25^{\circ}C$		1.9 (Note 2)			
		1.1 (Note 3)			
Operating Junction and Storage Temperature Range	$T_j; T_{stg}$	-55~+175		$^{\circ}C$	

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	25	$^{\circ}C/W$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	50	
		78 (Note 2)	
		135 (Note 3)	

- Note : 1.Pulse width limited by maximum junction temperature.
 2.Surface mounted on 1 in² copper pad of FR-4 board, pulse width $\leq 10s$, single operation.
 3.Surface mounted on minimum copper pad, pulse width $\leq 10s$, single operation.

N-Channel Electrical Characteristics ($T_C=25^{\circ}C$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	150	-	-	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_j$	-	0.14	-	V/ $^{\circ}C$	Reference to $25^{\circ}C, I_D=250\mu A$
$V_{GS(th)}$	1.3	-	2.3	V	$V_{DS}=V_{GS}, I_D=250\mu A$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
I_{DSS}	-	-	1	μA	$V_{DS}=120V, V_{GS}=0V$
	-	-	10	μA	$V_{DS}=120V, V_{GS}=0, T_j=55^{\circ}C$
* $R_{DS(ON)}$	-	169	230	m Ω	$I_D=1.8A, V_{GS}=10V$
	-	176	250		$I_D=1.5A, V_{GS}=4.5V$
* G_{FS}	-	7	-	S	$V_{DS}=10V, I_D=1.8A$
Dynamic					
C_{iss}	-	465	-	pF	$V_{DS}=25V, V_{GS}=0, f=1MHz$
C_{oss}	-	45	-		
C_{rss}	-	26	-		



*td(ON)	-	6.4	-	ns	V _{DS} =75V, I _D =1A, V _{GS} =10V, R _G =6Ω
*tr	-	16.4	-		
*td(OFF)	-	59.6	-		
*tf	-	60	-		
*Q _g	-	13.4	-	nC	V _{DS} =120V, I _D =1.8A, V _{GS} =10V
*Q _{gs}	-	1.6	-		
*Q _{gd}	-	3.5	-		
Body Diode					
*I _S	-	-	1.8	A	
*I _{SM}	-	-	10		
*V _{SD}	-	0.79	1.3	V	V _{GS} =0V, I _S =1.8A
trr *	-	28	-	ns	I _F =1.8A, dI _F /dt=100A/μs
Q _{rr} *	-	37	-	nC	

P-Channel Electrical Characteristics (T_c=25°C, unless otherwise specified)

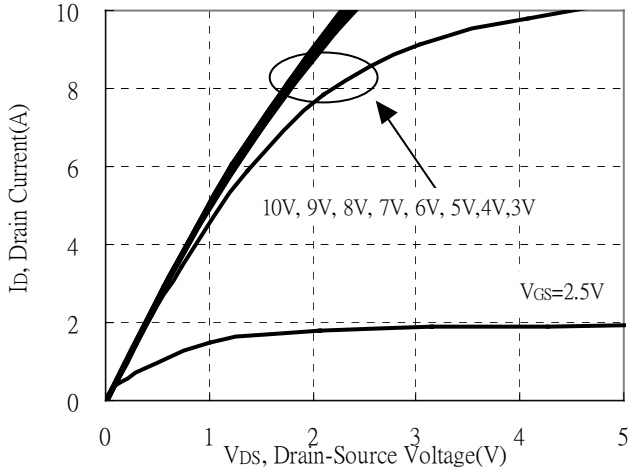
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-150	-	-	V	V _{GS} =0V, I _D =-250μA
ΔBV _{DSS} /ΔT _j	-	-0.12	-	V/°C	Reference to 25°C, I _D =-250μA
V _{GS(th)}	-1.3	-	-2.3	V	V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-120V, V _{GS} =0V
	-	-	-10		V _{DS} =-120V, V _{GS} =0, T _j =55°C
*R _{Ds(ON)}	-	259	340	mΩ	I _D =-1.5A, V _{GS} =-10V
	-	277	370		I _D =-1A, V _{GS} =-4.5V
*G _{FS}	-	5.8	-	S	V _{DS} =-10V, I _D =-1.5A
Dynamic					
C _{iss}	-	1053	-	pF	V _{DS} =-25V, V _{GS} =0, f=1MHz
C _{oss}	-	67	-		
C _{rss}	-	36	-		
*td(ON)	-	9	-	ns	V _{DS} =-75V, I _D =-1A, V _{GS} =-10V, R _G =6Ω
*tr	-	17.6	-		
*td(OFF)	-	55.4	-		
*tf	-	544	-		
*Q _g	-	25	-	nC	V _{DS} =-120V, I _D =-1.5A, V _{GS} =-10V
*Q _{gs}	-	3	-		
*Q _{gd}	-	6.3	-		
Body Diode					
*I _S	-	-	-1.5	A	
*I _{SM}	-	-	-8		
*V _{SD}	-	-0.76	-1.3	V	V _{GS} =0V, I _S =-1.5A
trr *	-	29	-	ns	I _F =1.5A, dI _F /dt=100A/μs
Q _{rr} *	-	36	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

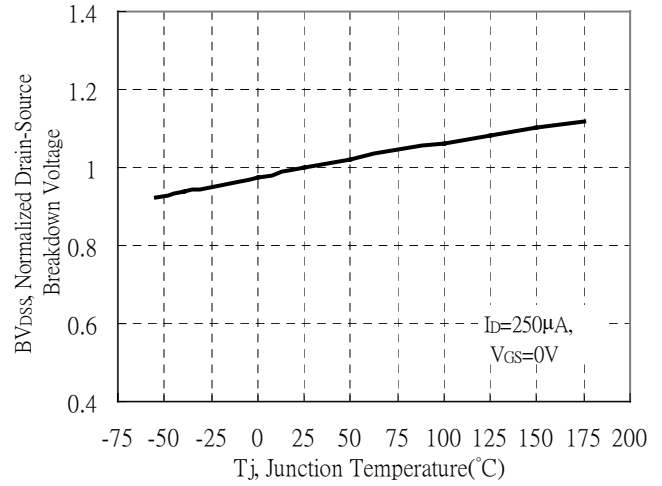


Typical Characteristics : Q1(N-channel)

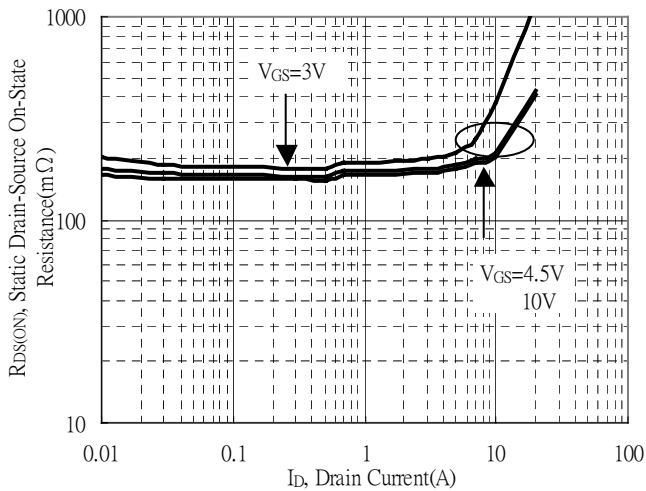
Typical Output Characteristics



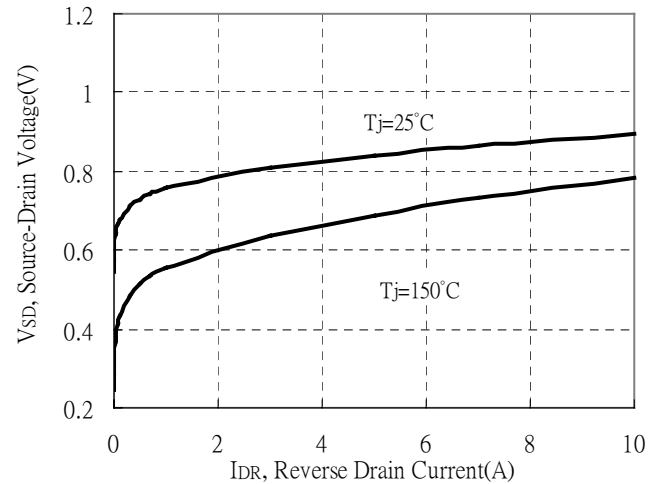
Brekdown Voltage vs Ambient Temperature



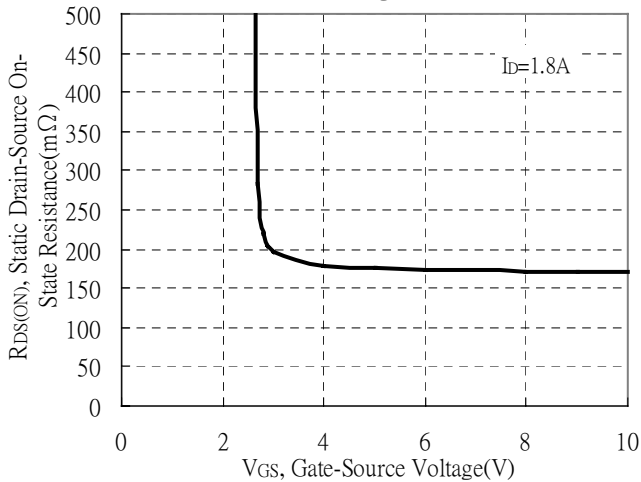
Static Drain-Source On-State resistance vs Drain Current



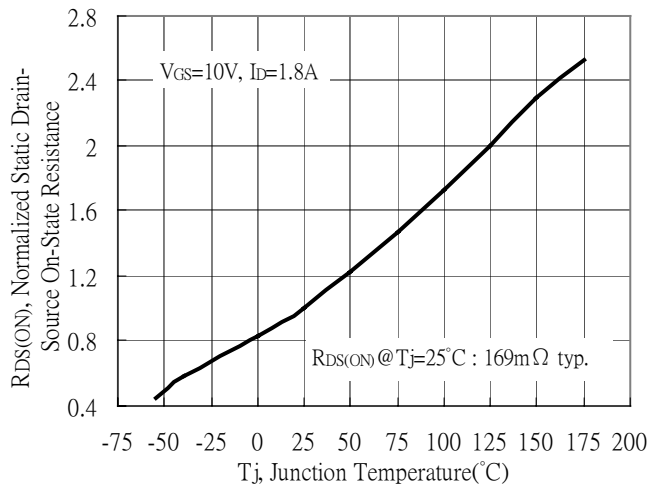
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

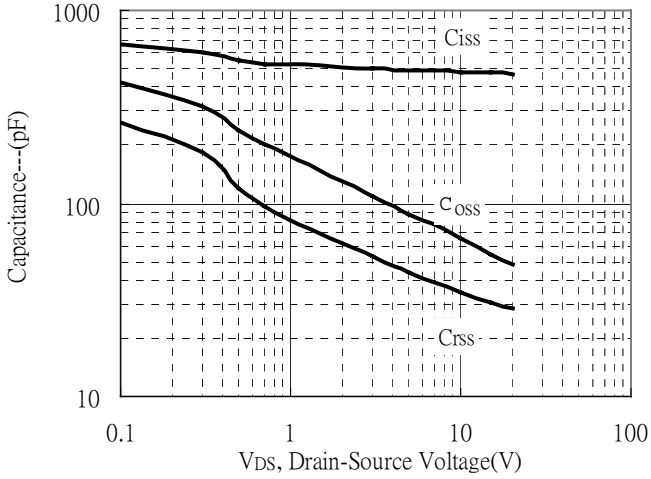


Drain-Source On-State Resistance vs Junction Temperature

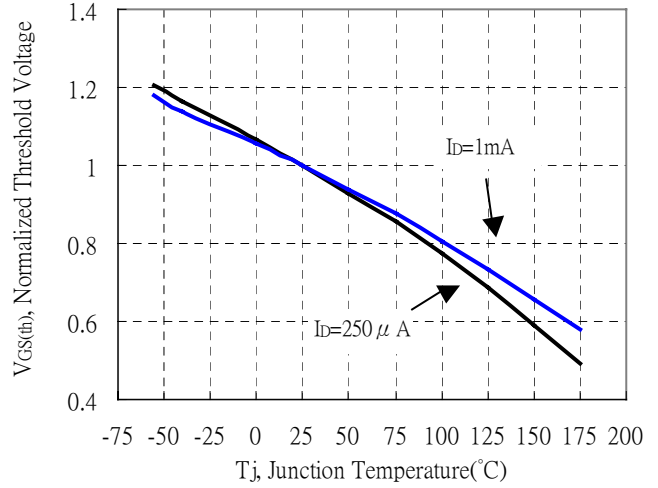


Typical Characteristics(Cont.) : Q1(N-channel)

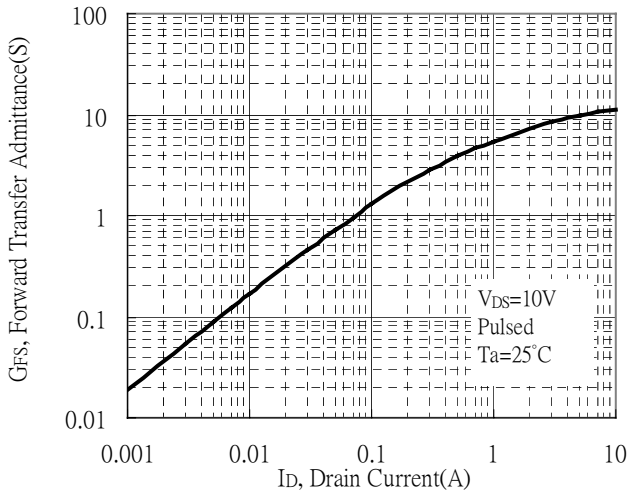
Capacitance vs Drain-to-Source Voltage



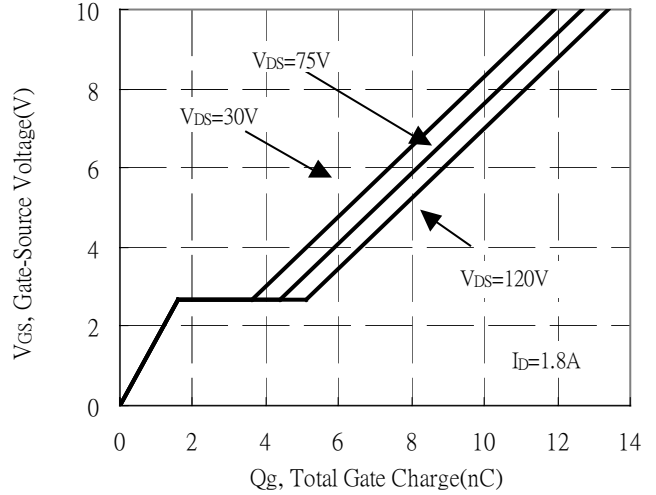
Threshold Voltage vs Junction Temperature



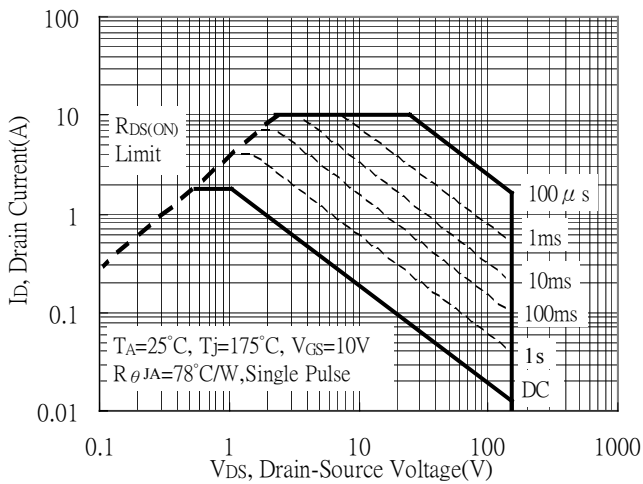
Forward Transfer Admittance vs Drain Current



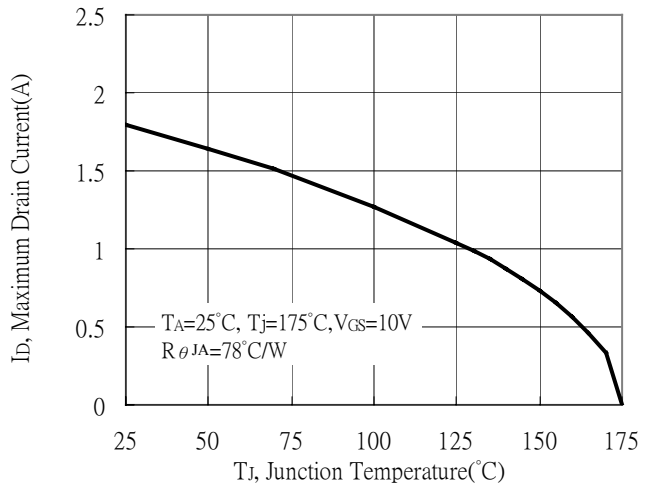
Gate Charge Characteristics



Maximum Safe Operating Area



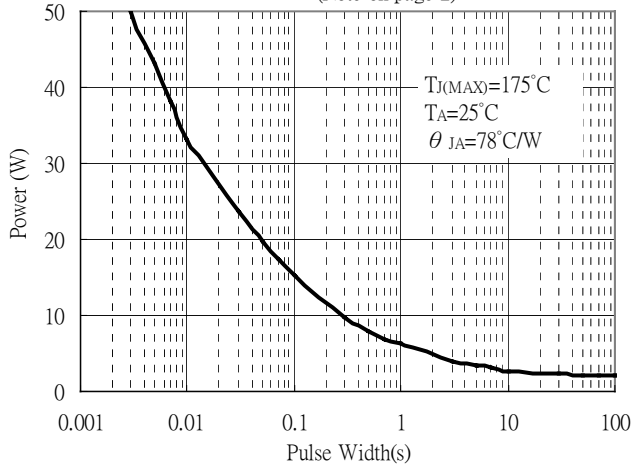
Maximum Drain Current vs Junction Temperature



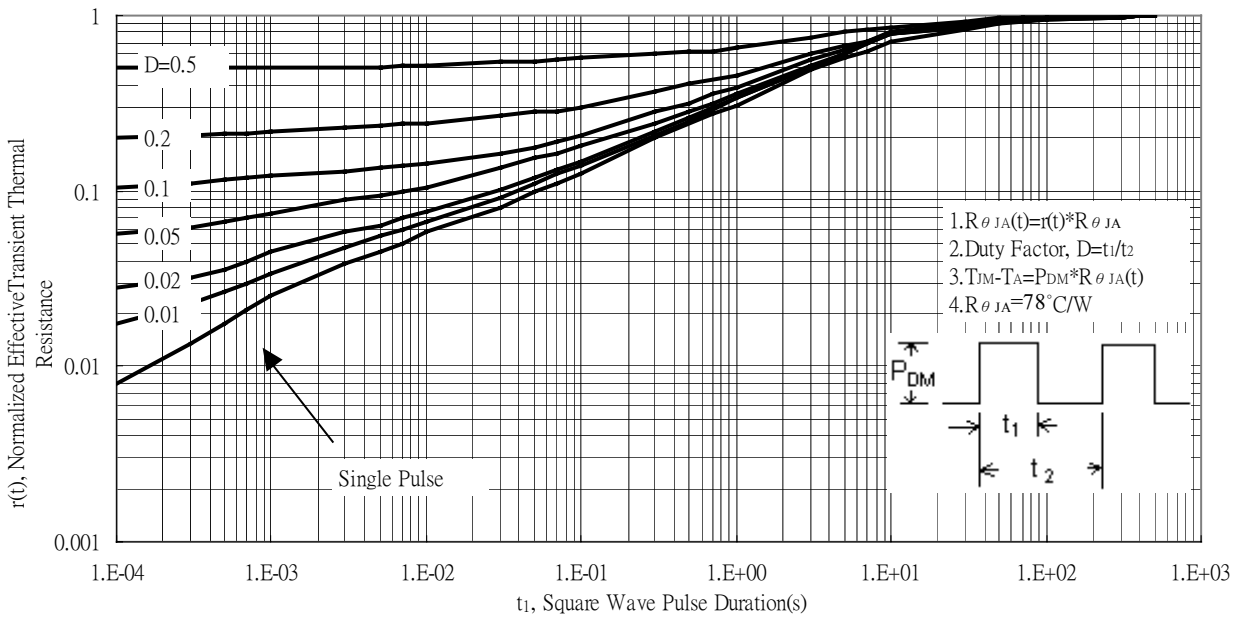


Typical Characteristics(Cont.) : Q1(N-channel)

Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



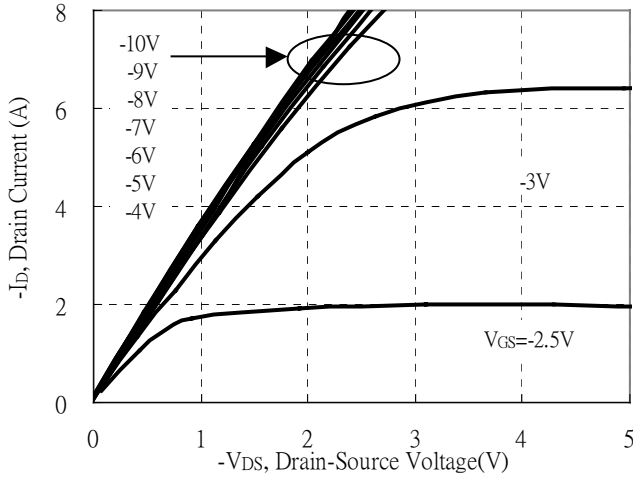
Transient Thermal Response Curves



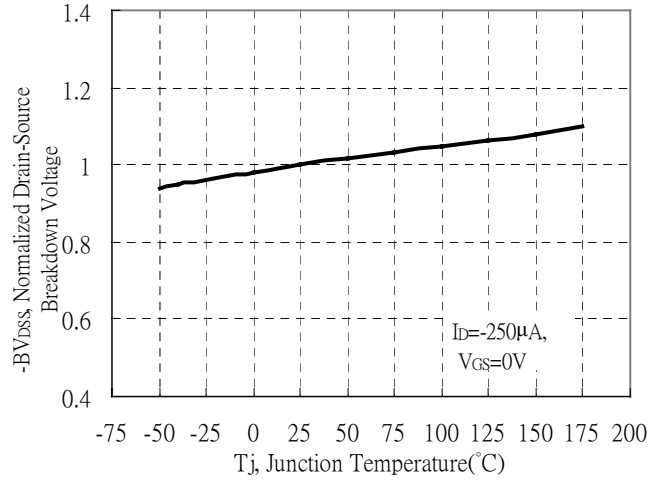


Typical Characteristics : Q2(P-channel)

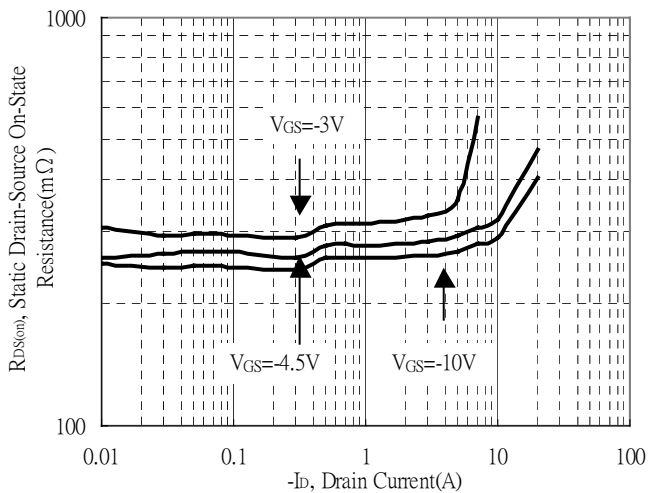
Typical Output Characteristics



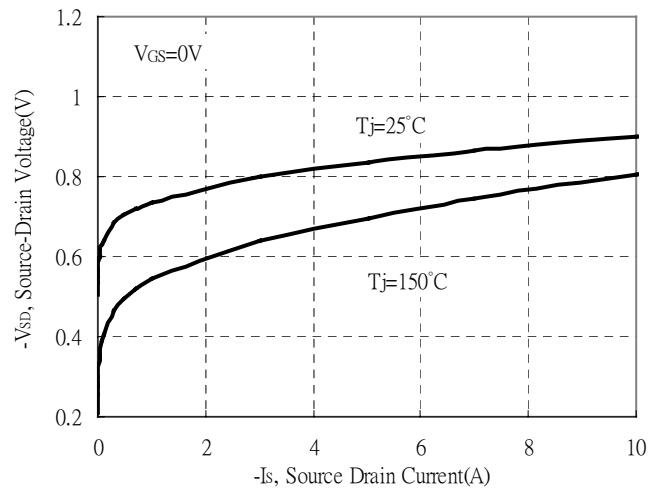
Breakdown Voltage vs Ambient Temperature



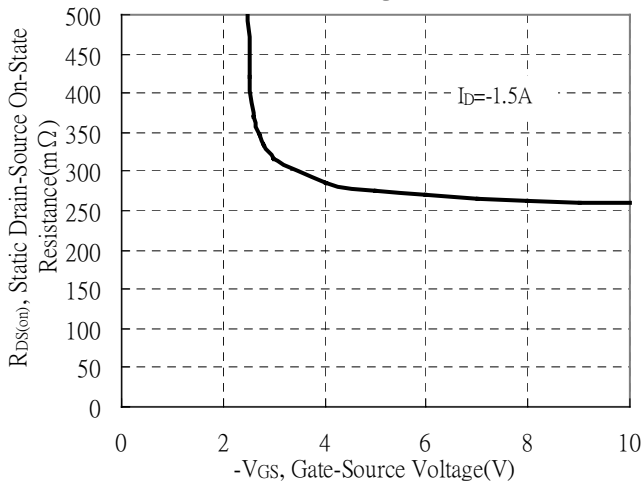
Static Drain-Source On-State resistance vs Drain Current



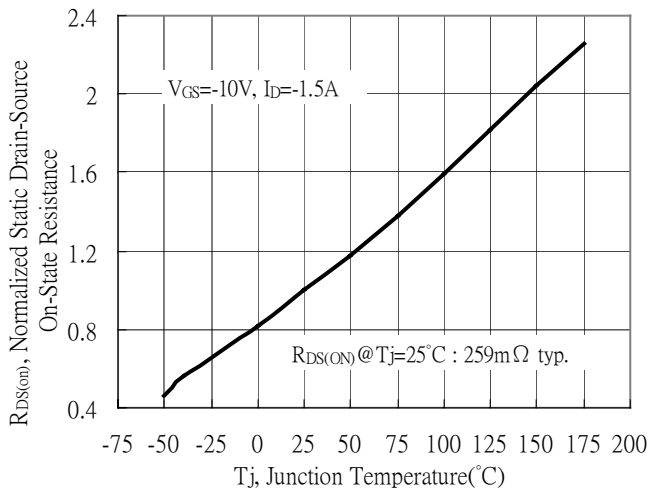
Source Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

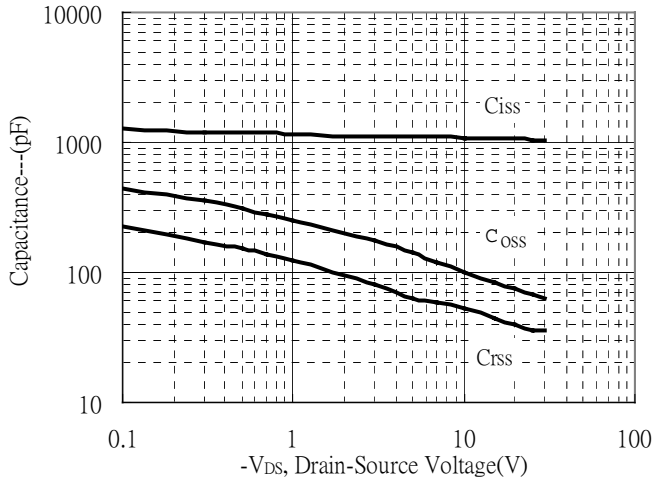


Drain-Source On-State Resistance vs Junction Temperature

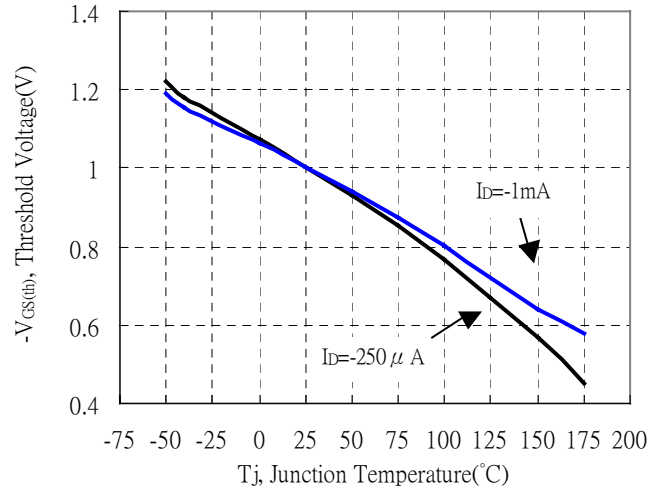


Typical Characteristics(Cont.) : Q2(P-channel)

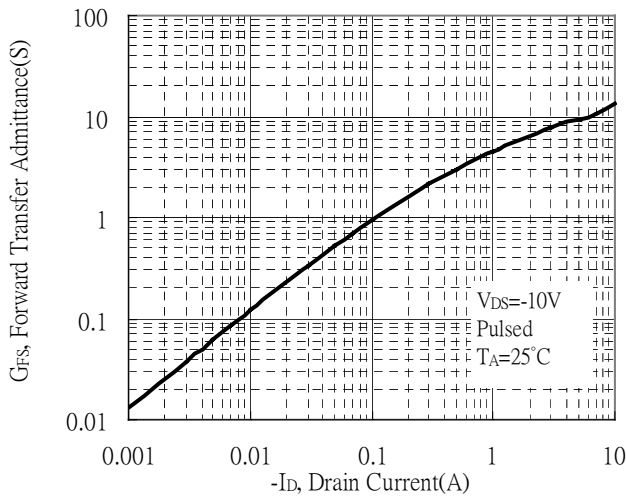
Capacitance vs Drain-to-Source Voltage



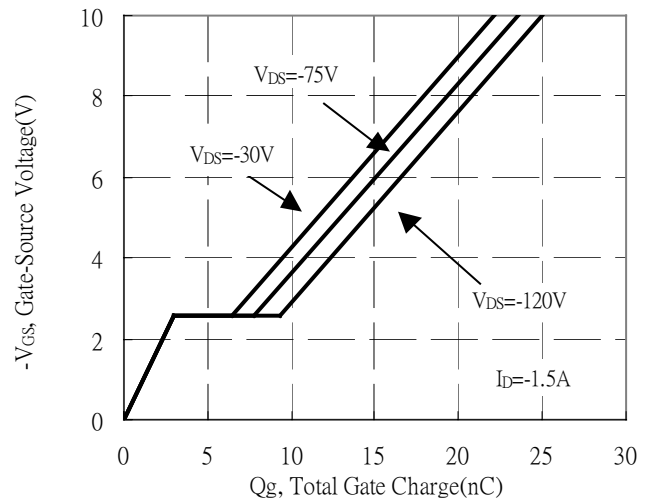
Threshold Voltage vs Junction Temperature



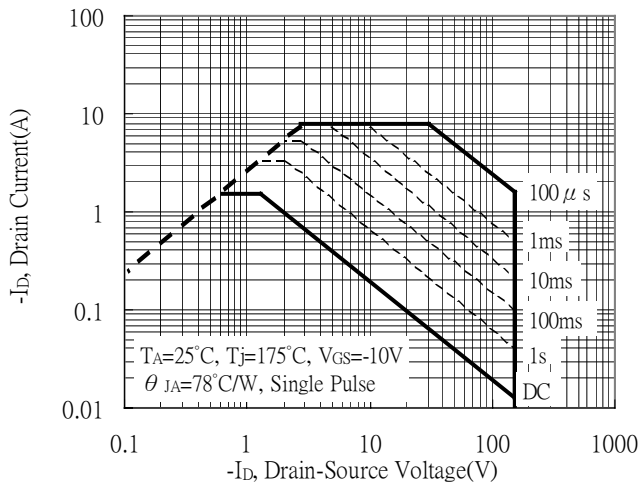
Forward Transfer Admittance vs Drain Current



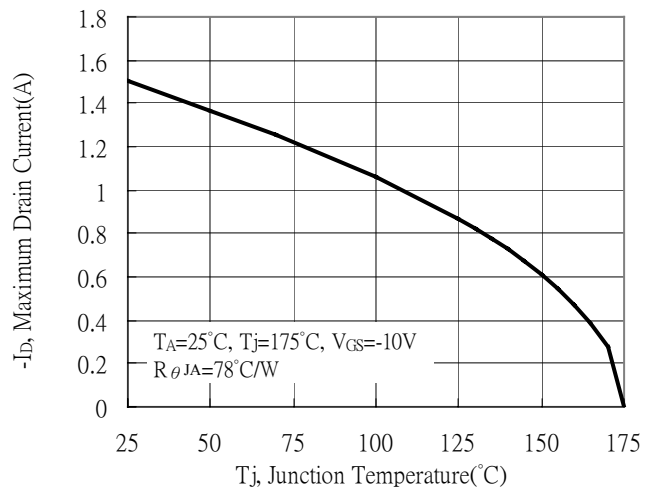
Gate Charge Characteristics



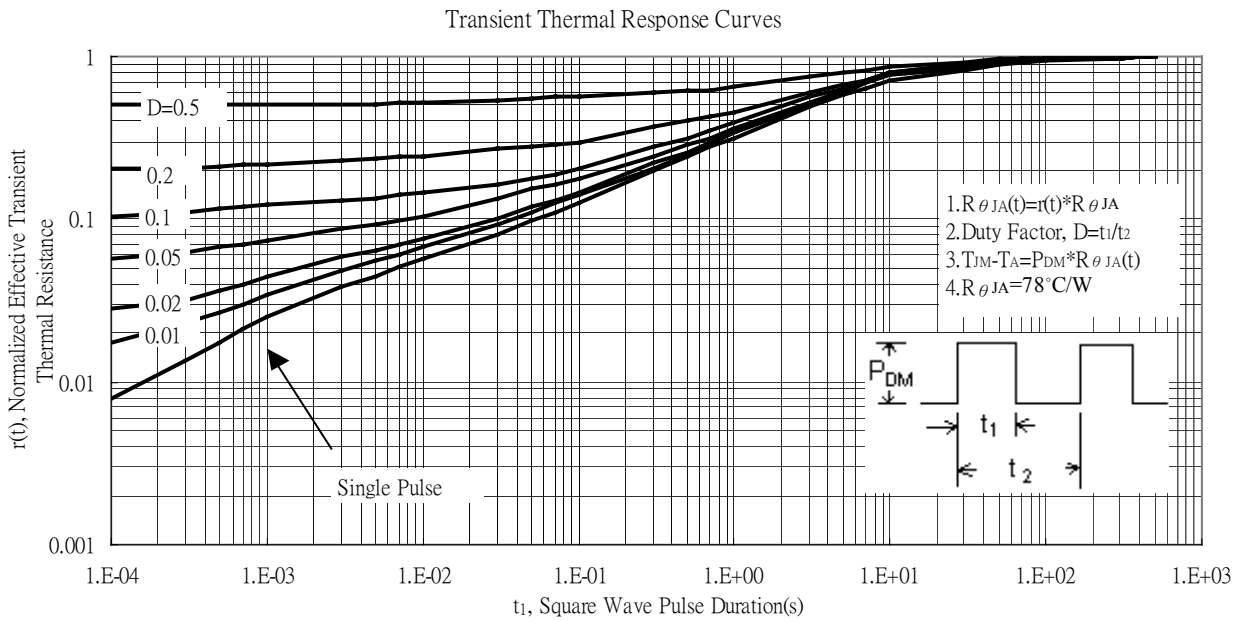
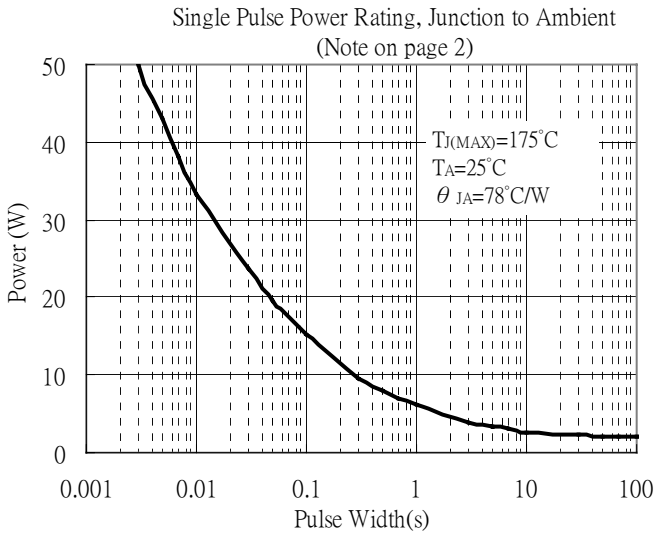
Maximum Safe Operating Area



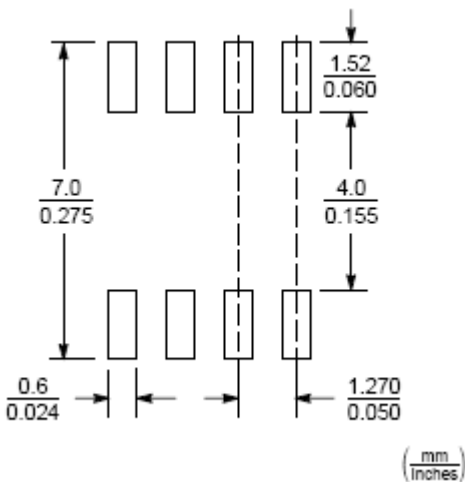
Maximum Drain Current vs Junction Temperature



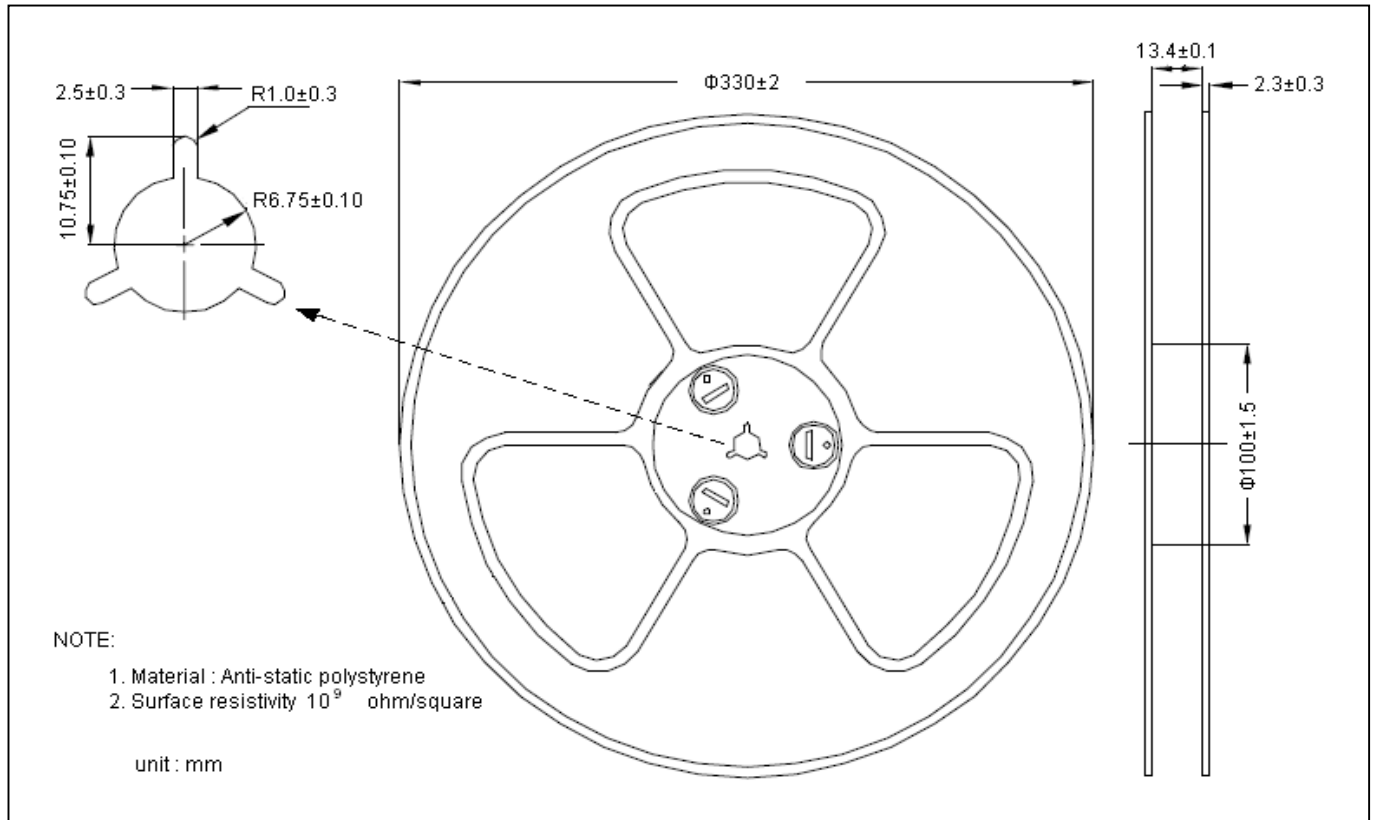
Typical Characteristics(Cont.) : Q2(P-channel)



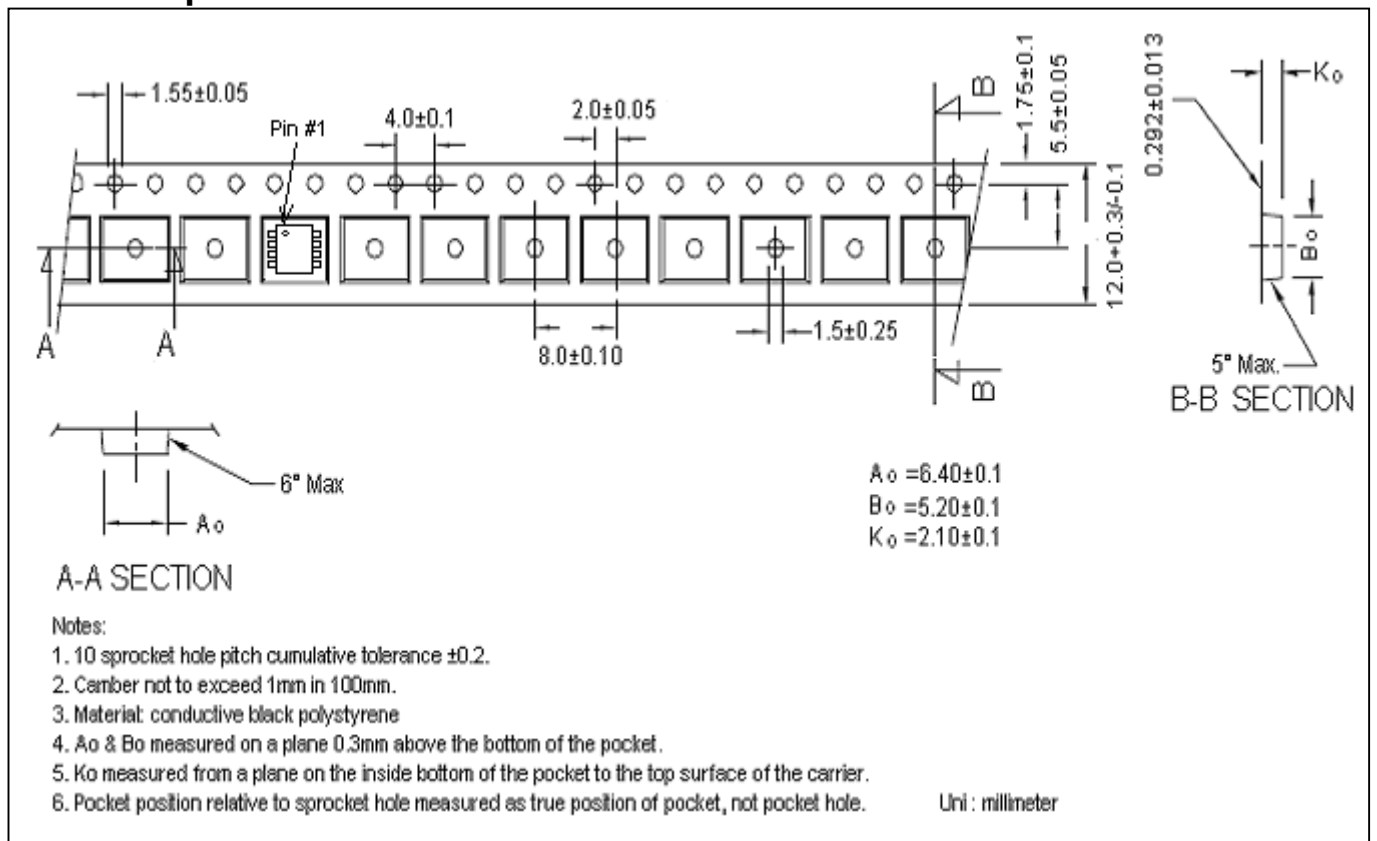
Recommended Soldering Footprint



Reel Dimension



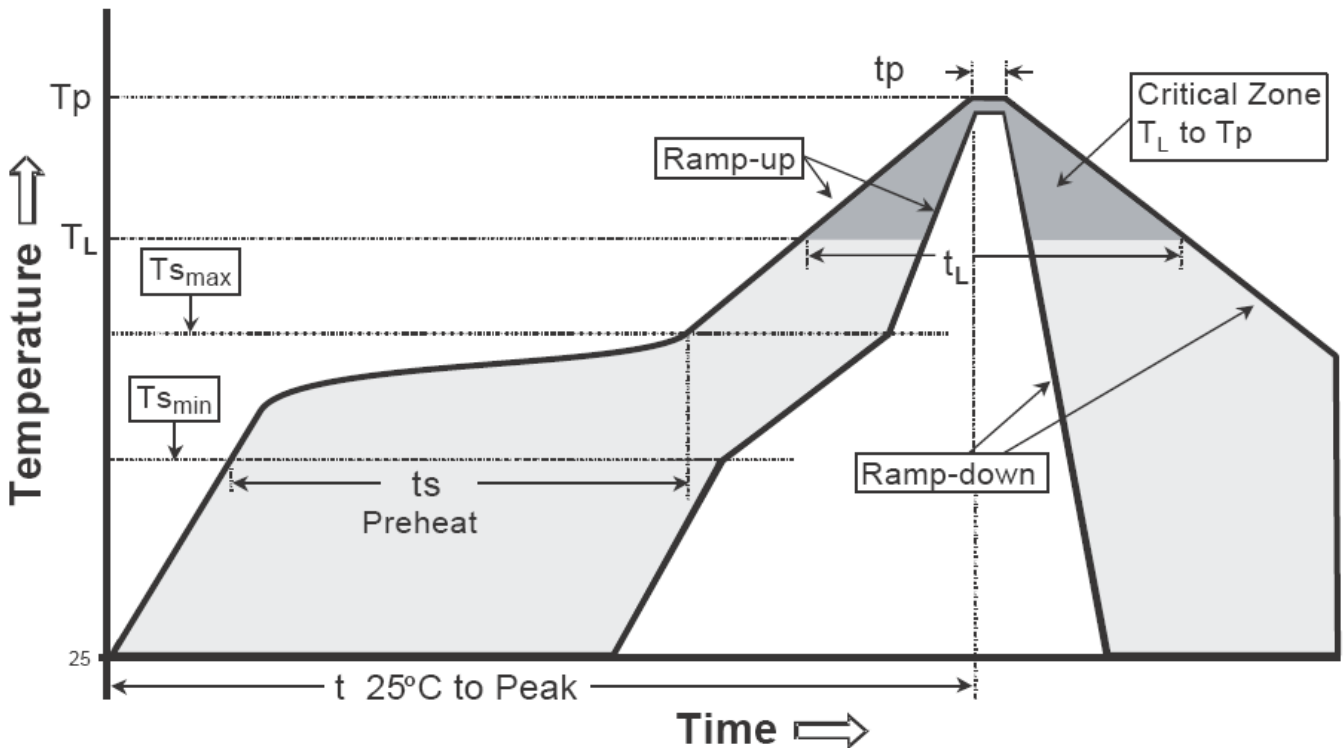
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

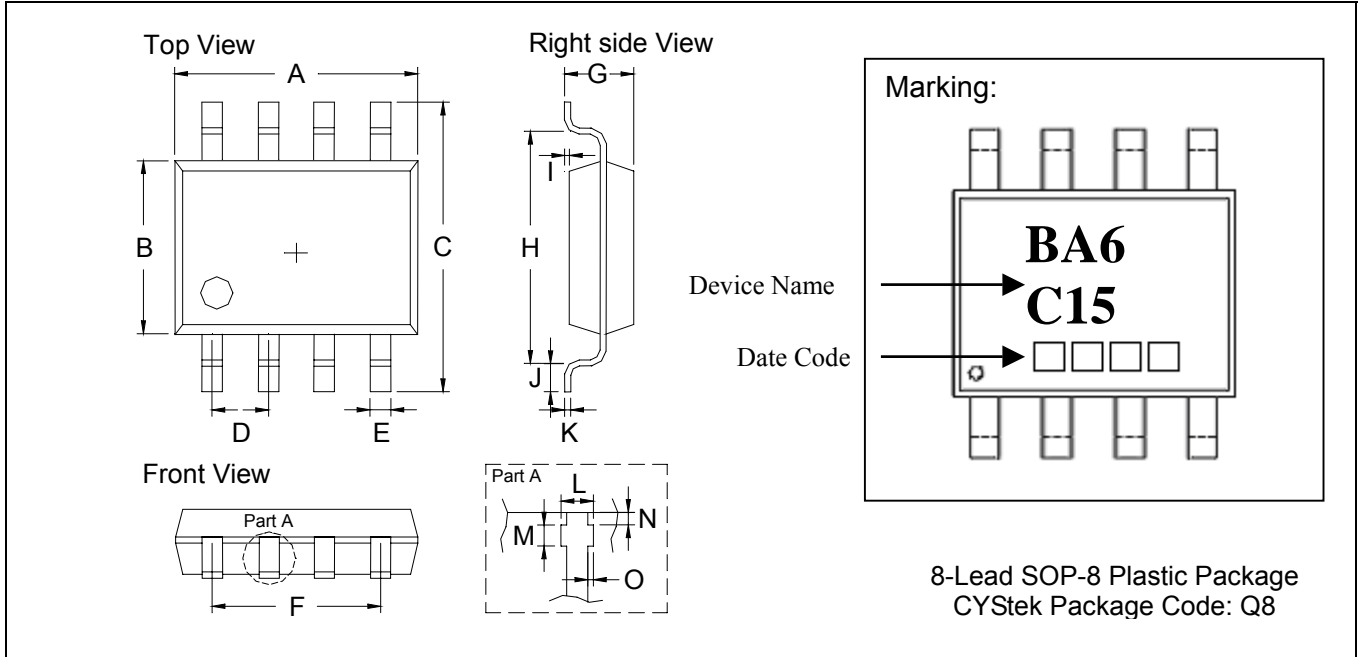
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOP-8 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1909	0.2007	4.85	5.10	I	0.0019	0.0078	0.05	0.20
B	0.1515	0.1555	3.85	3.95	J	0.0118	0.0275	0.30	0.70
C	0.2283	0.2441	5.80	6.20	K	0.0074	0.0098	0.19	0.25
D	0.0480	0.0519	1.22	1.32	L	0.0145	0.0204	0.37	0.52
E	0.0145	0.0185	0.37	0.47	M	0.0118	0.0197	0.30	0.50
F	0.1472	0.1527	3.74	3.88	N	0.0031	0.0051	0.08	0.13
G	0.0570	0.0649	1.45	1.65	O	0.0000	0.0059	0.00	0.15
H	0.1889	0.2007	4.80	5.10					

Notes: 1. Controlling dimension: millimeters.
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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